

IRF620SPbF

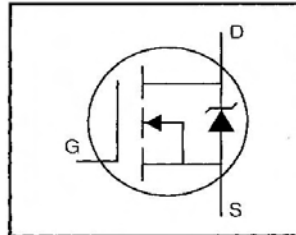
HEXFET® Power MOSFET

- Surface Mount
- Available in Tape & Reel
- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements

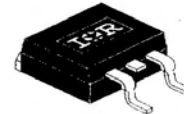
• Lead-Free
Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SMD-220 is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The SMD-220 is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.



$V_{DSS} = 200V$
 $R_{DS(on)} = 0.80\Omega$
 $I_D = 5.2A$



SMD-220

Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10 V$	5.2	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10 V$	3.3	
I_{DM}	Pulsed Drain Current ①	18	
$P_D @ T_C = 25^\circ C$	Power Dissipation	50	W
$P_D @ T_A = 25^\circ C$	Power Dissipation (PCB Mount)**	3.0	
	Linear Derating Factor	0.40	W/°C
	Linear Derating Factor (PCB Mount)**	0.025	
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②	110	mJ
I_{AR}	Avalanche Current ①	5.2	A
E_{AR}	Repetitive Avalanche Energy ①	5.0	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	2.5	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)**	—	—	40	
$R_{\theta JA}$	Junction-to-Ambient	—	—	62	

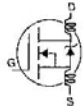
** When mounted on 1" square PCB (FR-4 or G-10 Material).

For recommended footprint and soldering techniques refer to application note #AN-994.

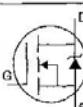
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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	200	—	—	V	$V_{GS}=0V, I_D=250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.29	—	$V/^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D=1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.80	Ω	$V_{GS}=10V, I_D=3.1A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
g_{fs}	Forward Transconductance	1.5	—	—	S	$V_{DS}=50V, I_D=3.1A$ ④
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS}=200V, V_{GS}=0V$
		—	—	250		$V_{DS}=160V, V_{GS}=0V, T_J=125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS}=20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS}=-20V$
Q_g	Total Gate Charge	—	—	14	nC	$I_D=4.8A$
Q_{gs}	Gate-to-Source Charge	—	—	3.0		$V_{DS}=160V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	7.9		$V_{GS}=10V$ See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	7.2	—	ns	$V_{DD}=100V$ $I_D=4.8A$ $R_G=18\Omega$ $R_D=20\Omega$ See Figure 10 ④
t_r	Rise Time	—	22	—		
$t_{d(off)}$	Turn-Off Delay Time	—	19	—		
t_f	Fall Time	—	13	—		
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6 mm (0.25in.) from package and center of die contact 
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	260	—	pF	$V_{GS}=0V$ $V_{DS}=25V$ $f=1.0\text{MHz}$ See Figure 5
C_{oss}	Output Capacitance	—	100	—		
C_{rss}	Reverse Transfer Capacitance	—	30	—		

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	5.2	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	18		
V_{SD}	Diode Forward Voltage	—	—	1.8	V	$T_J=25^\circ\text{C}, I_S=5.2A, V_{GS}=0V$ ④
t_{rr}	Reverse Recovery Time	—	150	300	ns	$T_J=25^\circ\text{C}, I_F=4.8A$
Q_{rr}	Reverse Recovery Charge	—	0.91	1.8	μC	$di/dt=100A/\mu\text{s}$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)
- ② $V_{DD}=50V$, starting $T_J=25^\circ\text{C}$, $L=6.1\text{mH}$
 $R_G=25\Omega, I_{AS}=5.2A$ (See Figure 12)
- ③ $I_{SD}\leq 5.2A, di/dt\leq 95A/\mu\text{s}, V_{DD}\leq V_{(BR)DSS}, T_J\leq 150^\circ\text{C}$
- ④ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

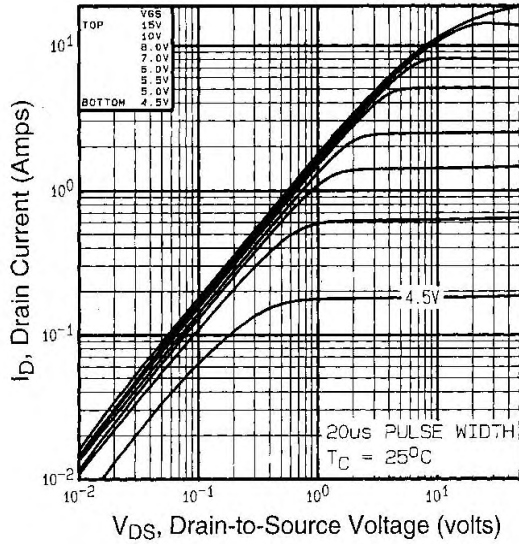


Fig 1. Typical Output Characteristics,
 $T_C=25^\circ\text{C}$

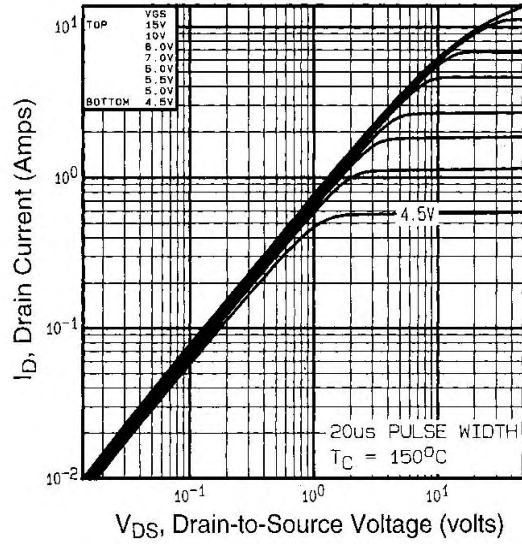


Fig 2. Typical Output Characteristics,
 $T_C=150^\circ\text{C}$

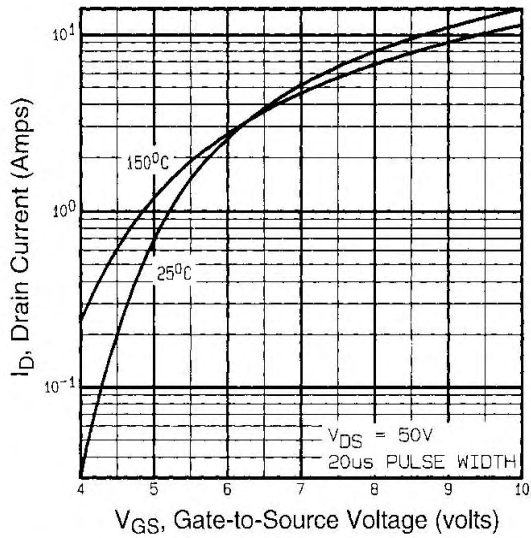


Fig 3. Typical Transfer Characteristics

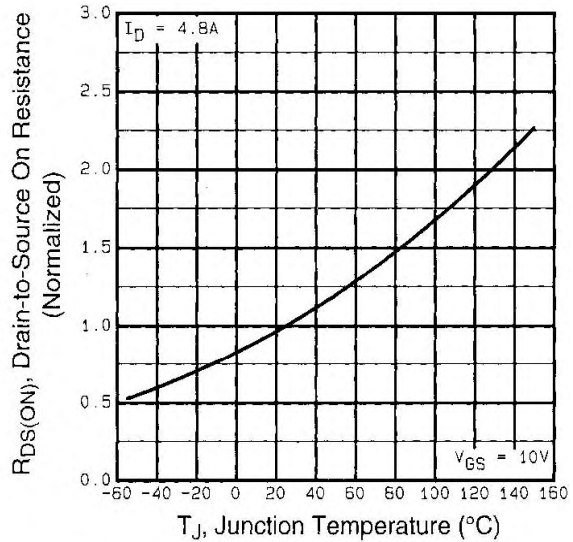


Fig 4. Normalized On-Resistance
Vs. Temperature

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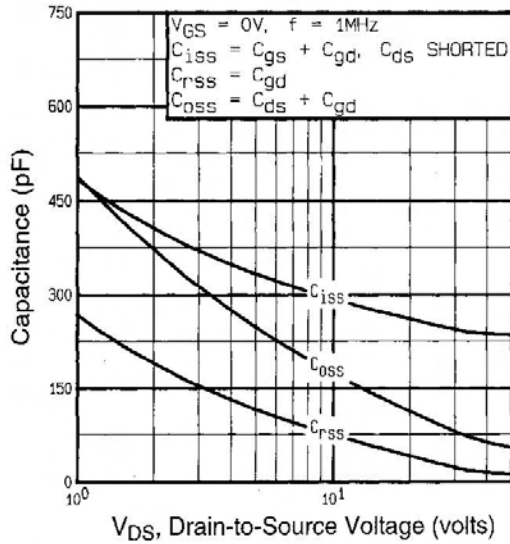


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

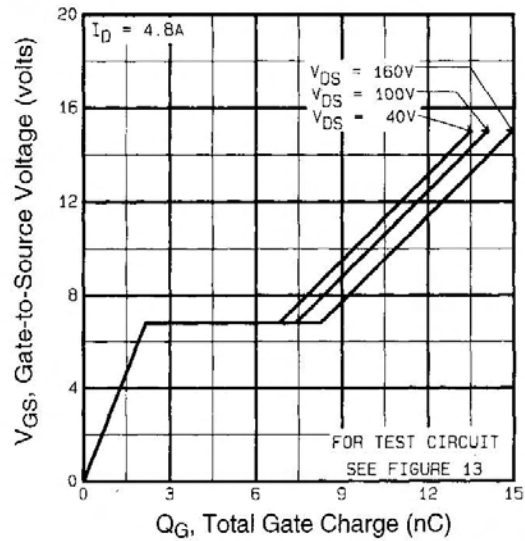


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

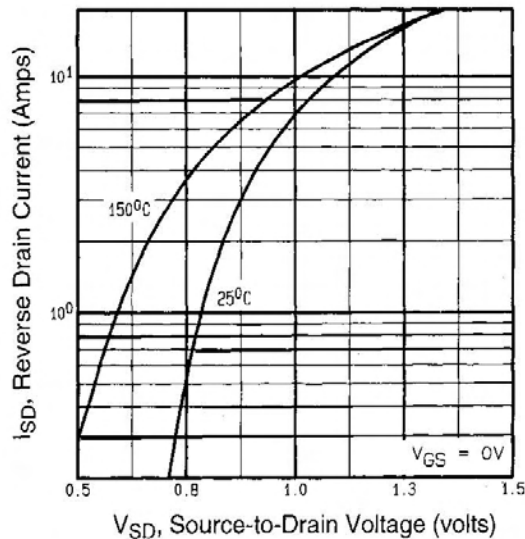


Fig 7. Typical Source-Drain Diode Forward Voltage

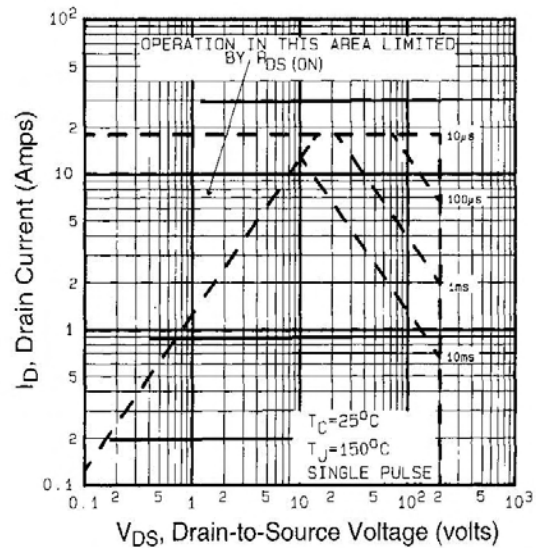


Fig 8. Maximum Safe Operating Area

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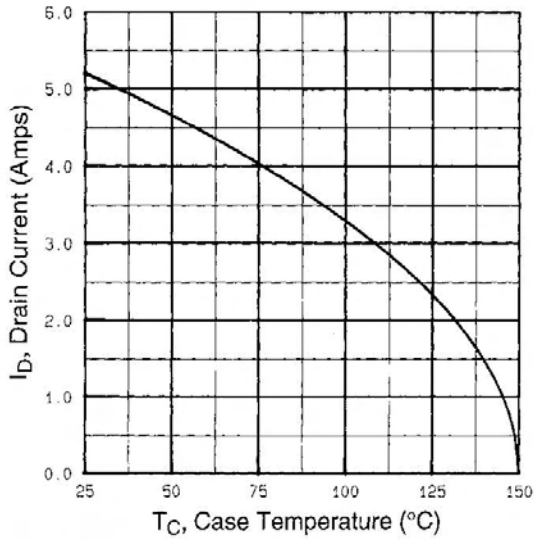


Fig 9. Maximum Drain Current Vs. Case Temperature

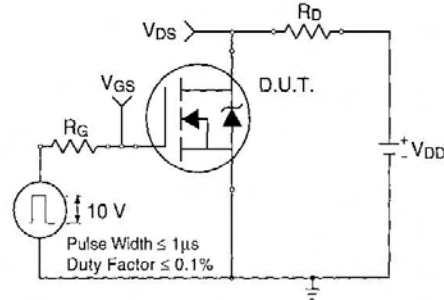


Fig 10a. Switching Time Test Circuit

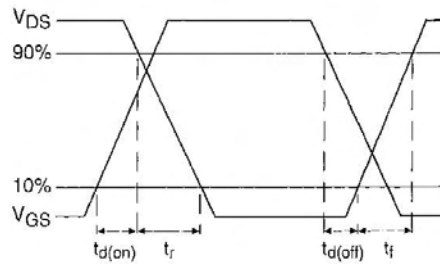


Fig 10b. Switching Time Waveforms

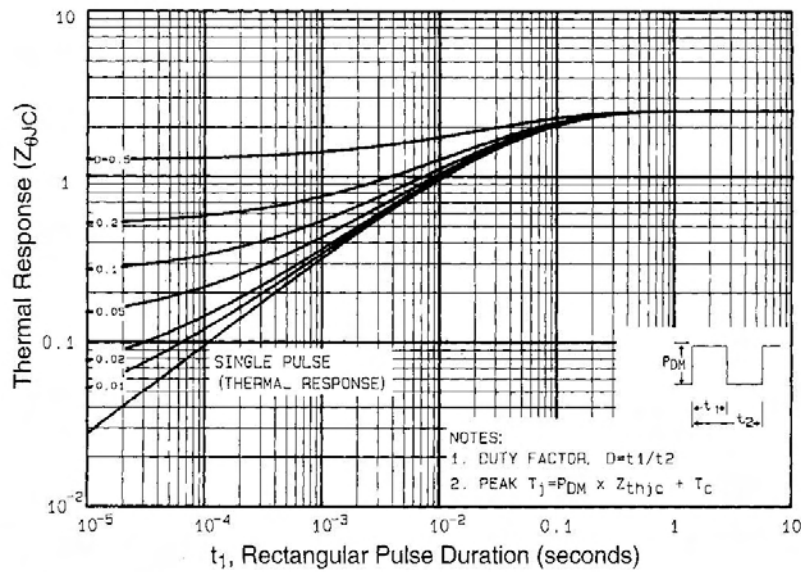


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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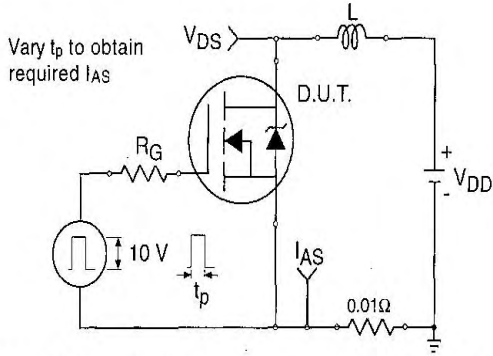


Fig 12a. Unclamped Inductive Test Circuit

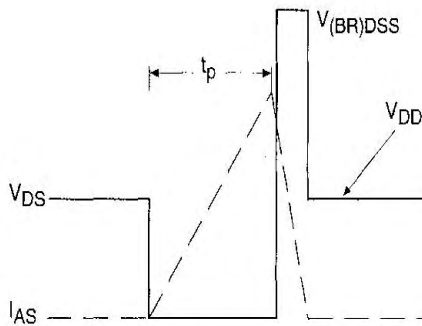


Fig 12b. Unclamped Inductive Waveforms

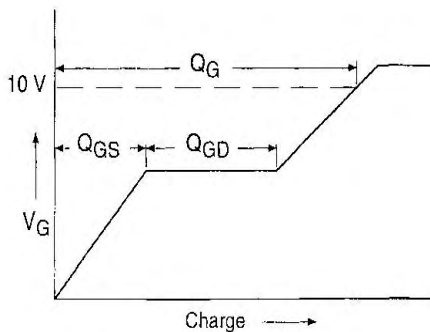


Fig 13a. Basic Gate Charge Waveform

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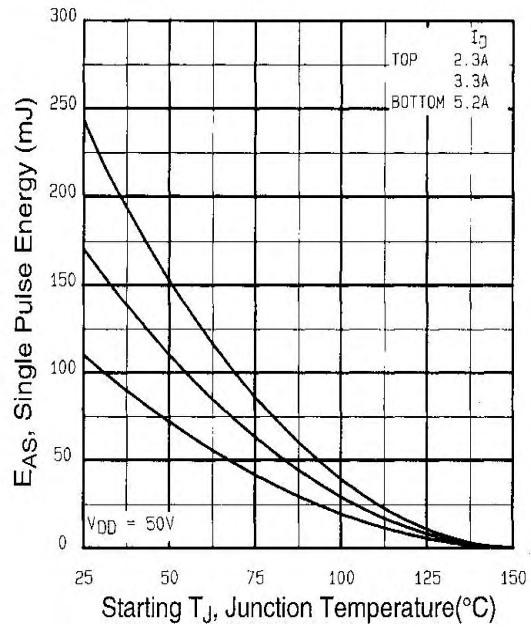


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

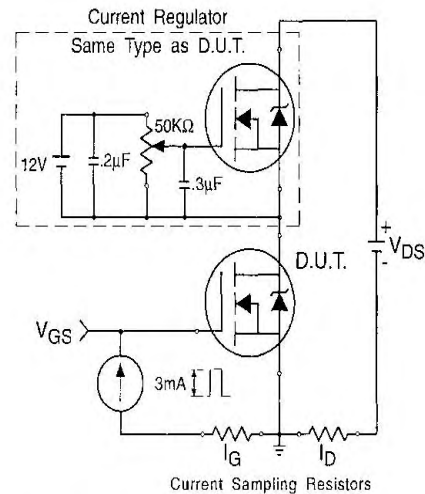
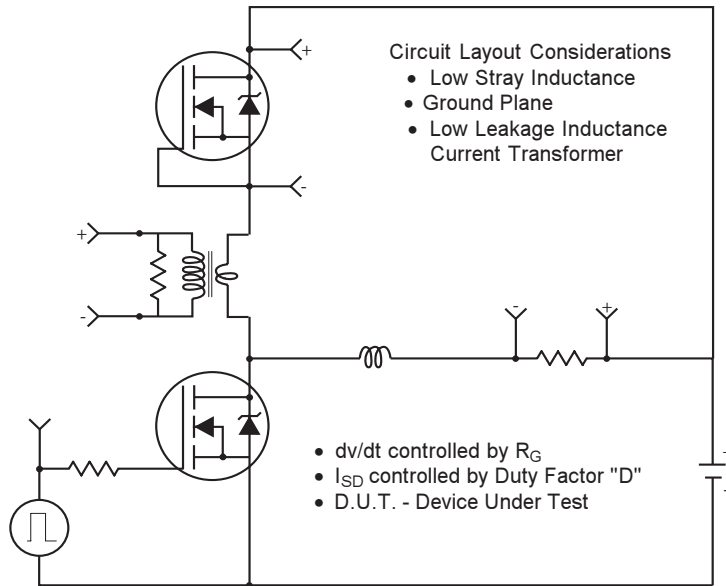


Fig 13b. Gate Charge Test Circuit

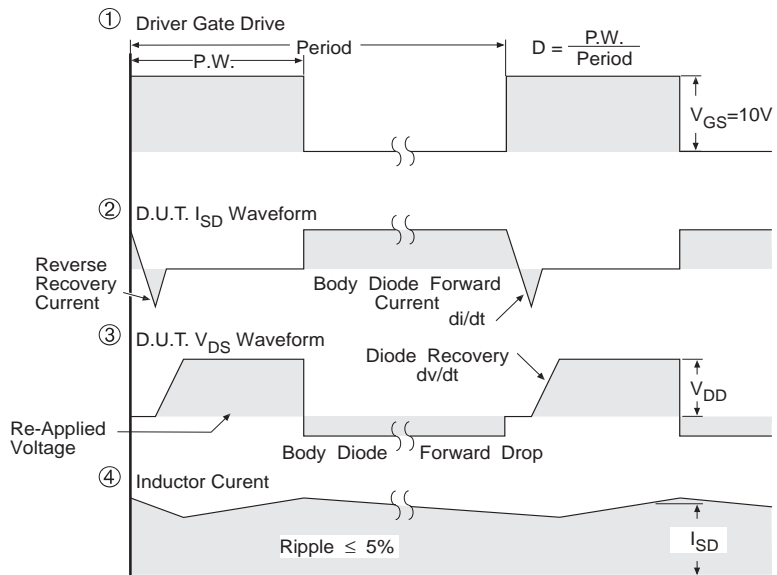
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Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity for P-Channel

** Use P-Channel Driver for P-Channel Measurements



*** $V_{GS} = 5.0V$ for Logic Level and 3V Drive Devices

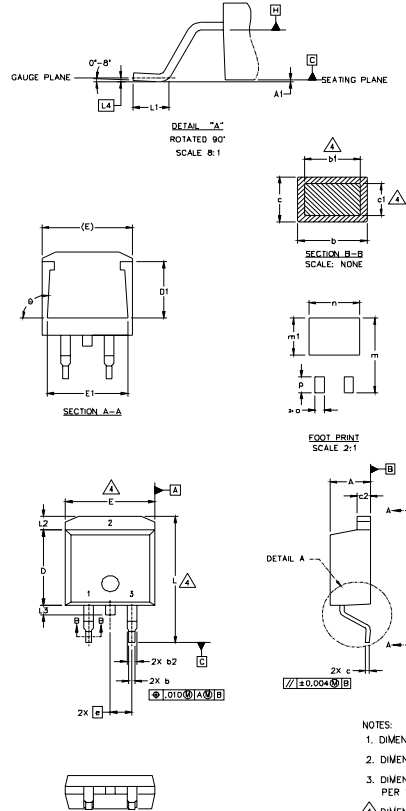
Fig-14 For N Channel HEXFETS

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D²Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1		0.127		.005	
b	0.51	0.99	.020	.039	4
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	4
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		3
E	9.65	10.67	.380	.420	
E1	6.22		.245		3
e	2.54 BSC		.100 BSC		
L	14.61	15.88	.575	.625	4
L1	1.78	2.79	.070	.110	
L2		1.65		.065	4
L3	1.27	1.78	.050	.070	
L4	0.25 BSC		.010 BSC		4
m	17.78		.700		
m1	8.89		.350		4
n	11.43		.450		
o	2.08		.082		4
p	3.81		.150		
θ	90°	93°	90°	93°	

LEAD ASSIGNMENTS

HEXFET	IGBTs, CoPACK	DIODES
1.- GATE	1.- GATE	1.- ANODE *
2.- DRAIN	2.- COLLECTOR	2.- CATHODE
3.- SOURCE	3.- EMITTER	3.- ANODE

* PART DEPENDENT.

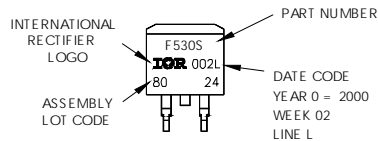
NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
- CONTROLLING DIMENSION: INCH.

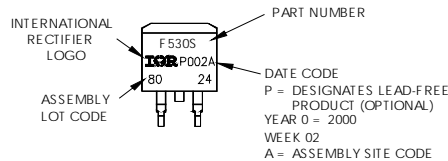
D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line
position indicates "Lead-Free"

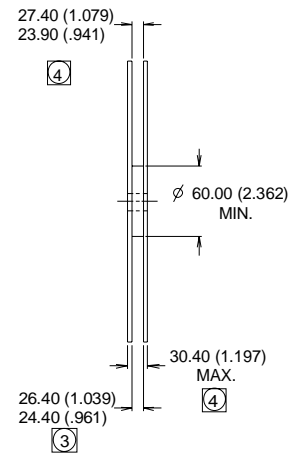
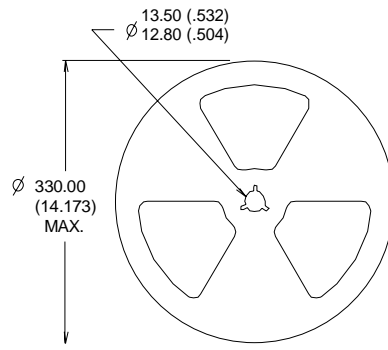
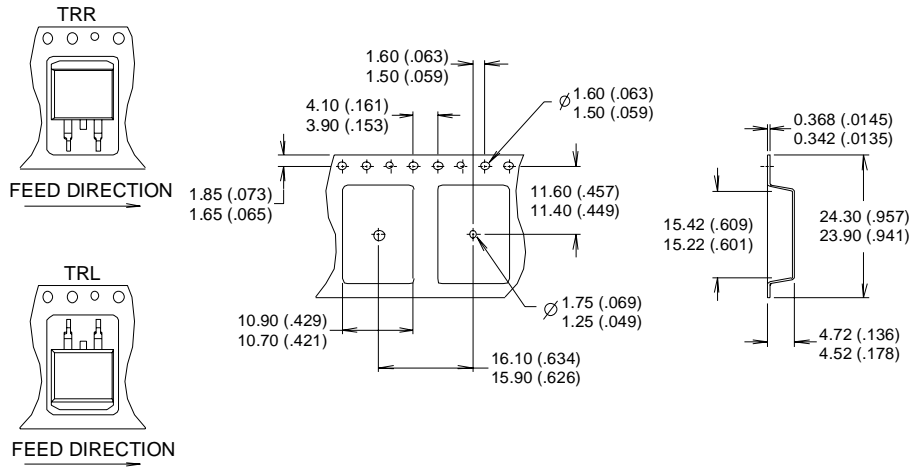


OR



D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONFORMS TO EIA-418.
 2. CONTROLLING DIMENSION: MILLIMETER.
 - ③ DIMENSION MEASURED @ HUB.
 - ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Data and specifications subject to change without notice.